

# MBR4045PT

## SWITCHMODE™ Power Rectifier

### Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 40 A Total (20 A Per Diode Leg)
- Pb-Free Package is Available\*

### Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

### Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets UL 94, V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B  
Machine Model C

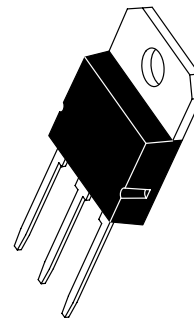
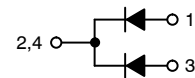
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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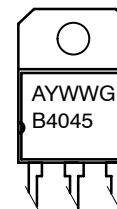
<http://onsemi.com>

## SCHOTTKY BARRIER RECTIFIER 40 AMPERES 45 VOLTS



SOT-93  
CASE 340D  
STYLE 2

### MARKING DIAGRAM



B4045 = Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping†
MBR4045PT	SOT-93	30 Units/Rail
MBR4045PTG	SOT-93 (Pb-Free)	30 Units/Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MBR4045PT

## MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	45	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 125^\circ\text{C}$ ) Per Diode Per Device	$I_{F(AV)}$	20 40	A
Peak Repetitive Forward Current, (Rated $V_R$ , Square Wave, 20 kHz @ $T_C = 90^\circ\text{C}$ ) Per Diode	$I_{FRM}$	40	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	$I_{FSM}$	400	A
Peak Repetitive Reverse Current, (2.0 $\mu\text{s}$ , 1.0 kHz)	$I_{RRM}$	2.0	A
Storage Temperature Range	$T_{stg}$	-65 to +175	$^\circ\text{C}$
Operating Junction Temperature (Note 1)	$T_J$	-65 to +175	$^\circ\text{C}$
Peak Surge Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	175	$^\circ\text{C}$
Voltage Rate of Change	$dv/dt$	10,000	V/ $\mu\text{s}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

## THERMAL CHARACTERISTICS

Characteristic	Conditions	Symbol	Max	Unit
Maximum Thermal Resistance, Junction-to-Case	Minimum Pad	$R_{\theta JC}$	1.4	$^\circ\text{C/W}$
Maximum Thermal Resistance, Junction-to-Ambient	Minimum Pad	$R_{\theta JA}$	55	

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (Note 2) ( $i_F = 20\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $i_F = 20\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $i_F = 40\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $i_F = 40\text{ A}$ , $T_J = 125^\circ\text{C}$ )	$V_F$	-	0.53 0.46 0.64 0.62	0.70 0.60 0.80 0.75	V
Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_J = 25^\circ\text{C}$ ) (Rated DC Voltage, $T_J = 125^\circ\text{C}$ )	$i_R$	-	0.09 30	1.0 50	mA

# MBR4045PT

## TYPICAL ELECTRICAL CHARACTERISTICS

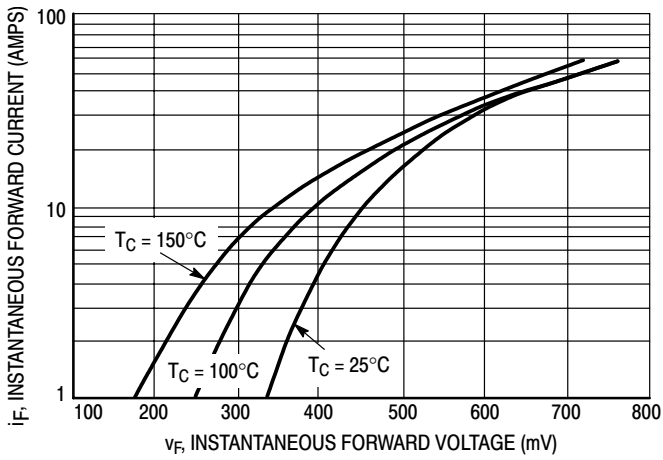


Figure 1. Typical Forward Voltage

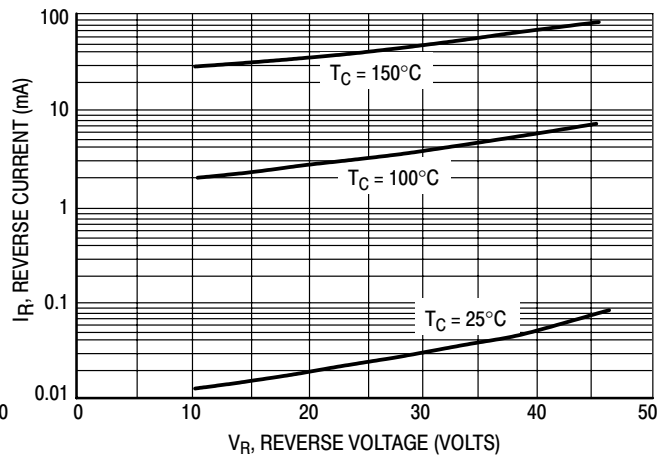


Figure 2. Typical Reverse Current

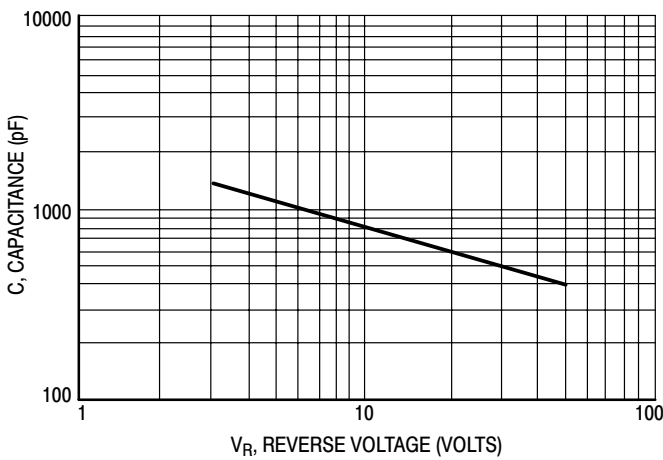


Figure 3. Typical Capacitance Per Leg

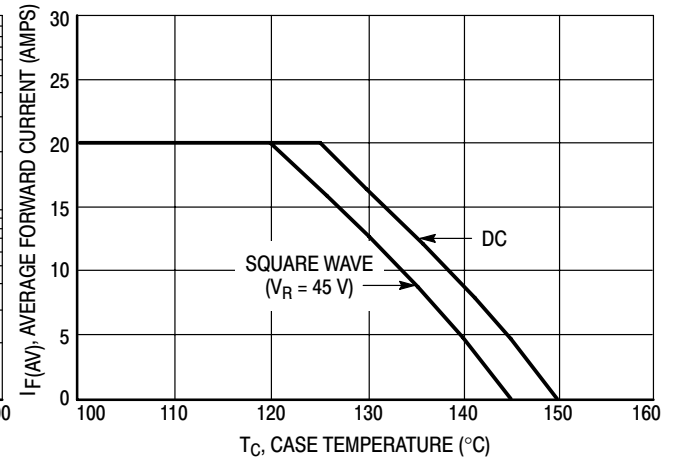


Figure 4. Current Derating Per Leg

# MECHANICAL CASE OUTLINE

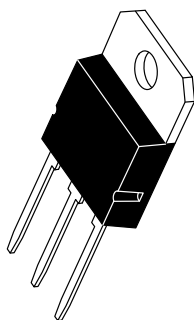
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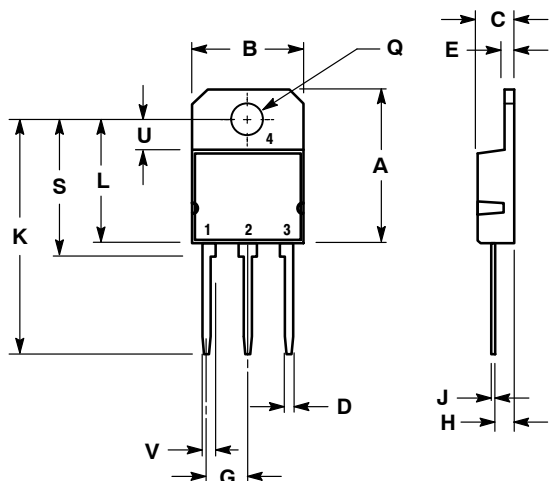


### SOT-93 (TO-218) CASE 340D-02 ISSUE E

DATE 01/03/2002



SCALE 1:1



STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

STYLE 2:  
PIN 1. ANODE  
2. CATHODE  
3. ANODE  
4. CATHODE

- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  - CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
xxxxx = Device Code

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